

Product Summary

BV _{SSS}	R _{SS(ON)} Max	I _S T _A = +25°C
12V	2.75mΩ @ V _{GS} = 4.5V	24.4A
	6.1mΩ @ V _{GS} = 2.5V	16.4A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{SS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

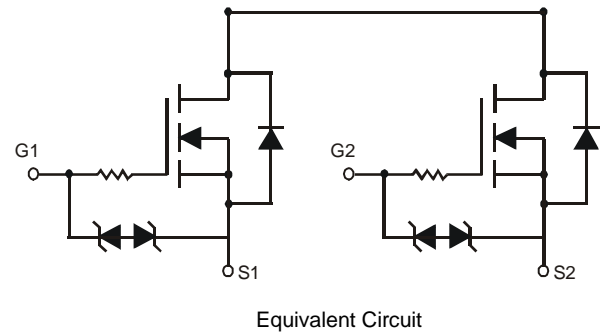
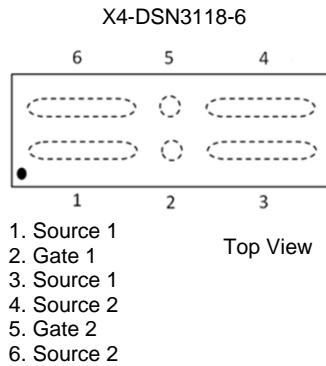
- Battery Management
- Load Switch
- Battery Protection

Features

- CSP with Footprint 3.05mm × 1.77mm
- Height = 0.11mm for Low Profile
- ESD Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: X4-DSN3118-6
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu. Solderable per MIL-STD-202, Method 208 (e4)

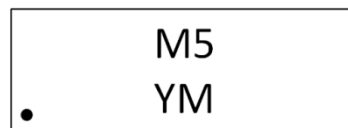


Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1002UCA6-7	X4-DSN3118-6	3000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



M5 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: F = 2018)
 M or \bar{M} = Month (ex: 9 = September)

Date Code Key

Year	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Source-Source Voltage			V_{SSS}	12	V
Gate-Source Voltage			V_{GSS}	± 8	V
Continuous Source Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_S	24.4	A
		$T_A = +70^\circ\text{C}$		19.6	
Continuous Source Current (Note 5) $V_{GS} = 2.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$	I_S	16.4	A
		$T_A = +70^\circ\text{C}$		13.1	
Pulsed Source Current (Note 6)			I_{SM}	100	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P_D	1.10	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 7)	$R_{\theta JA}$	114.1	$^\circ\text{C/W}$
Power Dissipation (Note 5)	P_D	2.47	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^\circ\text{C}$ (Note 5)	$R_{\theta JA}$	50.7	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Source-Source Breakdown Voltage	BV_{SSS}	12	—	—	V	$V_{GS} = 0\text{V}, I_S = 1\text{mA}$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{SSS}	—	—	1	μA	$V_{SS} = 9.6\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 8\text{V}, V_{SS} = 0\text{V}$
		—	—	± 1.0	μA	$V_{GS} = \pm 5\text{V}, V_{SS} = 0\text{V}$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.35	0.8	1.4	V	$V_{SS} = 10\text{V}, I_S = 1.41\text{mA}$
Static Source-Source On-Resistance	$R_{SS(ON)}$	1.5	2.27	2.75	m Ω	$V_{GS} = 4.5\text{V}, I_S = 6\text{A}$
		1.6	2.36	2.85		$V_{GS} = 3.8\text{V}, I_S = 6\text{A}$
		1.7	2.54	3.95		$V_{GS} = 3.1\text{V}, I_S = 6\text{A}$
		1.9	2.9	6.1		$V_{GS} = 2.5\text{V}, I_S = 6\text{A}$
Diode Forward Voltage	V_{SS}	—	0.69	1.2	V	$V_{GS} = 0\text{V}, I_S = 6\text{A}$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{ISS}	—	3062	4593	pF	$V_{SS} = 10\text{V}, V_{GS} = 0\text{V}, f = 1\text{kHz}$
Output Capacitance	C_{OSS}	—	758	1137		
Reverse Transfer Capacitance	C_{RSS}	—	198	297		
Total Gate Charge	Q_g	—	45.7	68.6	nC	$V_{SS} = 8\text{V}, V_{GS} = 4\text{V}, I_S = 6\text{A}$
Gate-Source Charge	Q_{gs}	—	8.3	12.5		
Gate-Drain Charge	Q_{gd}	—	16.0	24.0		
Gate Charge at V_{TH}	$Q_{g(th)}$	—	4.5	6.8		
Turn-On Delay Time	$t_{D(ON)}$	—	1005	1508	ns	$V_{SS} = 8\text{V}, V_{GS} = 4\text{V}, I_S = 6\text{A}$
Turn-On Rise Time	t_R	—	2186	3279		
Turn-Off Delay Time	$t_{D(OFF)}$	—	2643	3965		
Turn-Off Fall Time	t_F	—	4193	6290		

- Notes:
- Device mounted on FR-4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 - Repetitive rating, pulse width limited by junction temperature.
 - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

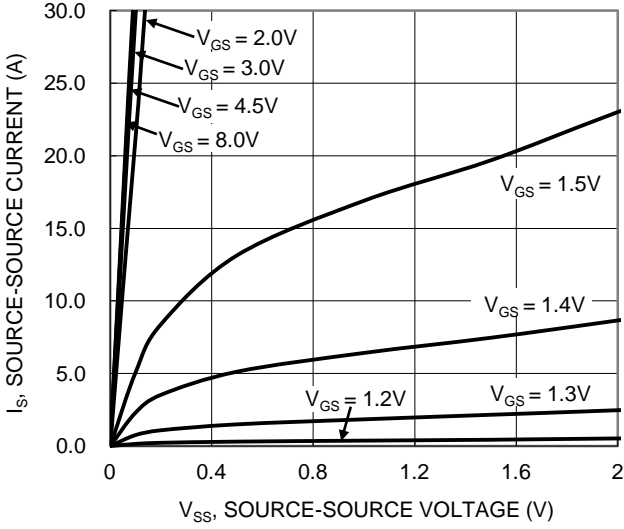


Figure 1. Typical Output Characteristic

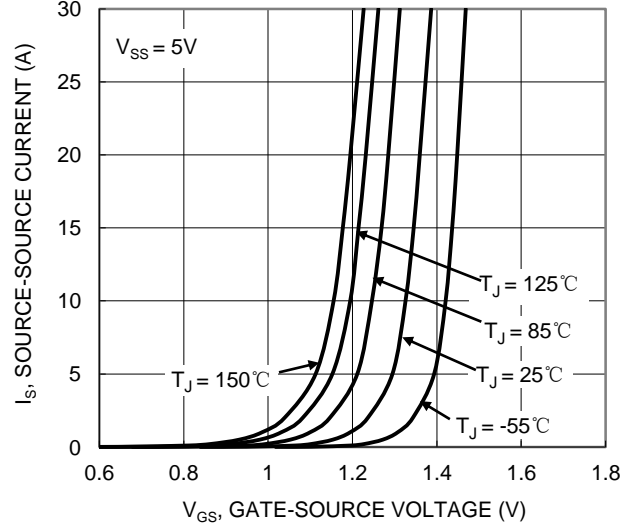


Figure 2. Typical Transfer Characteristic

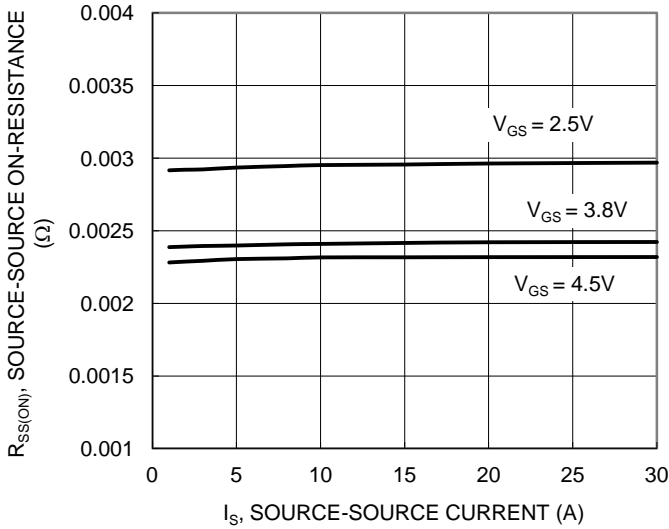


Figure 3. Typical On-Resistance vs. Source Current and Gate Voltage

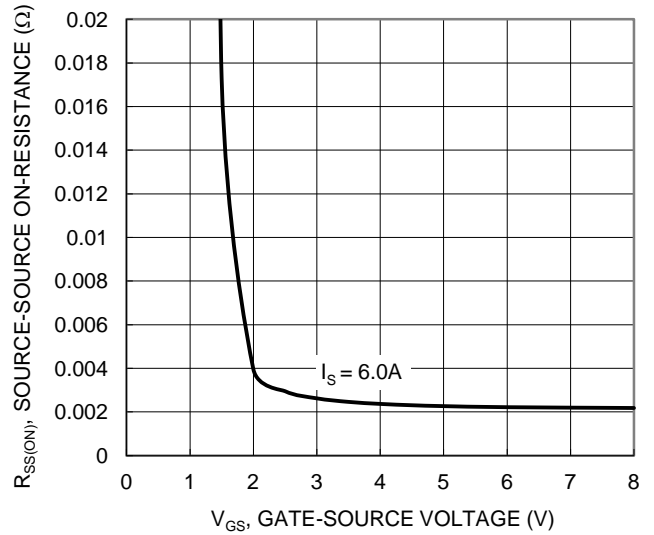


Figure 4. Typical Transfer Characteristic

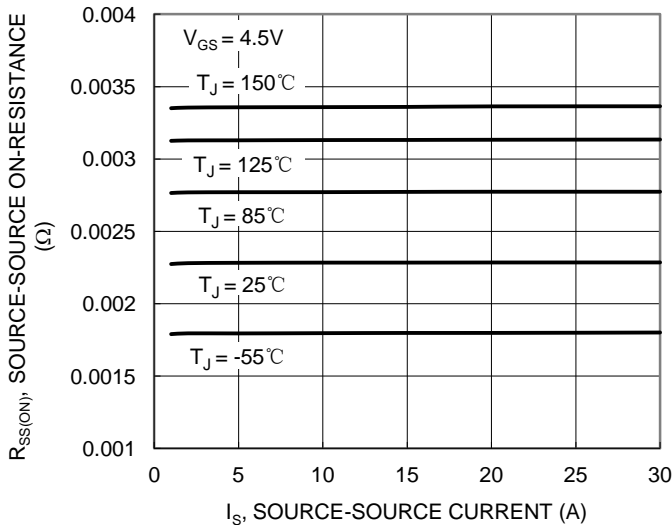


Figure 5. Typical On-Resistance vs. Source Current and Junction Temperature

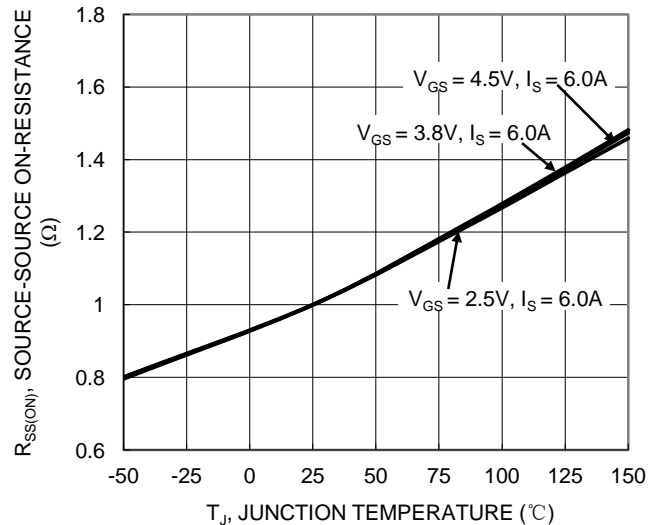


Figure 6. On-Resistance Variation with Junction Temperature

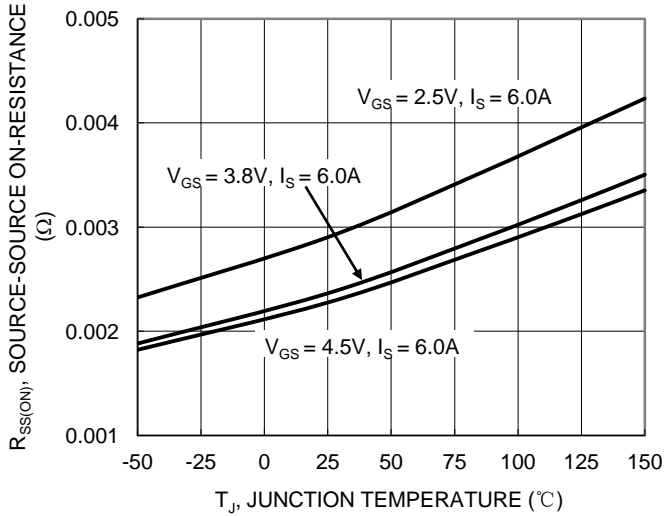


Figure 7. On-Resistance Variation with Junction Temperature

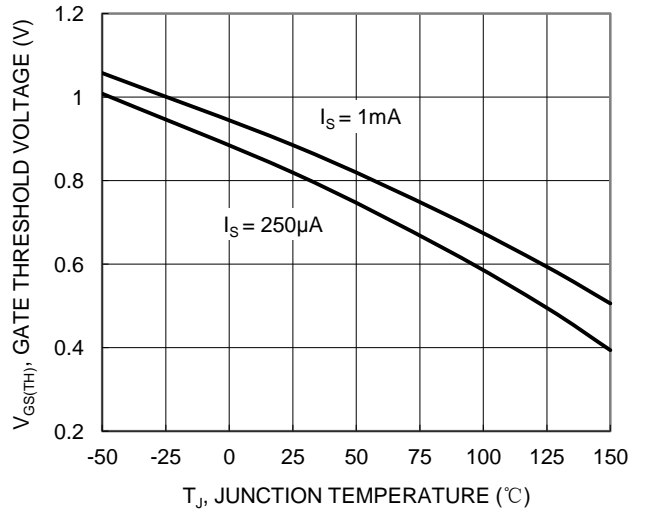


Figure 8. Gate Threshold Variation vs. Junction Temperature

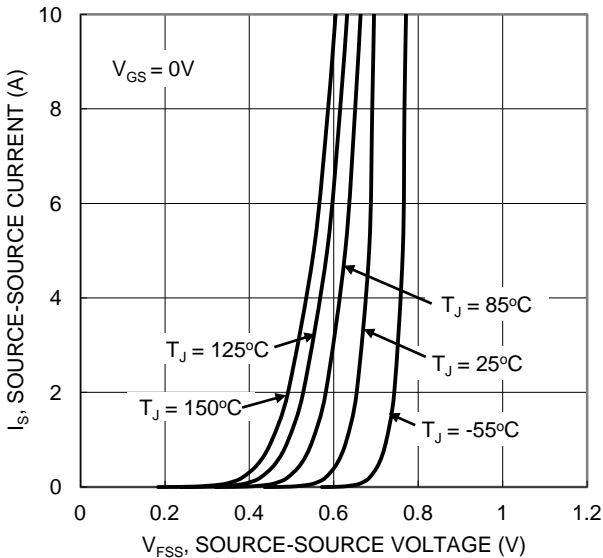


Figure 9. Diode Forward Voltage vs. Current

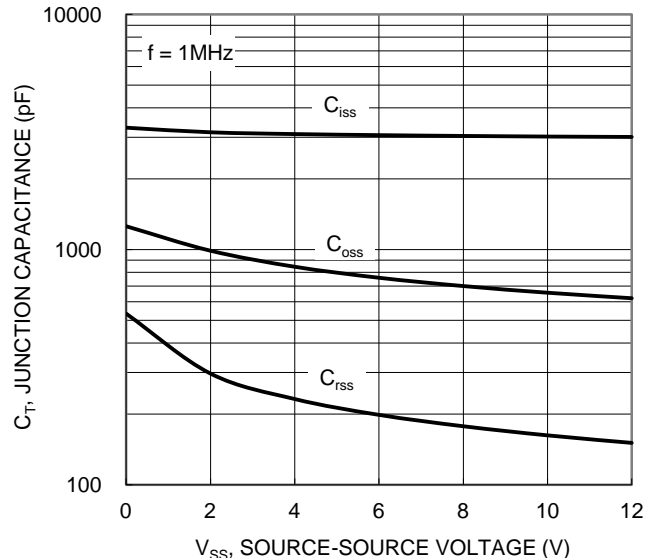


Figure 10. Typical Junction Capacitance

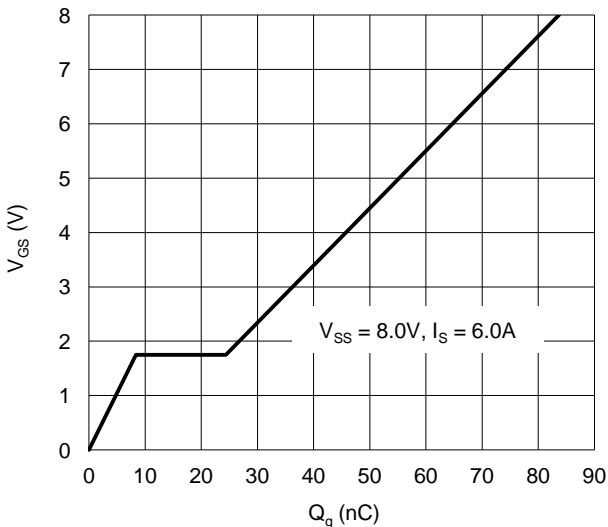


Figure 11. Gate Charge

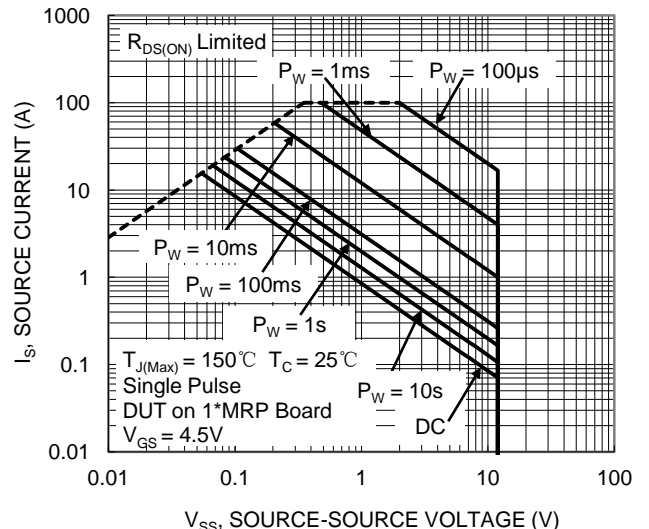


Figure 12. SOA, Safe Operation Area

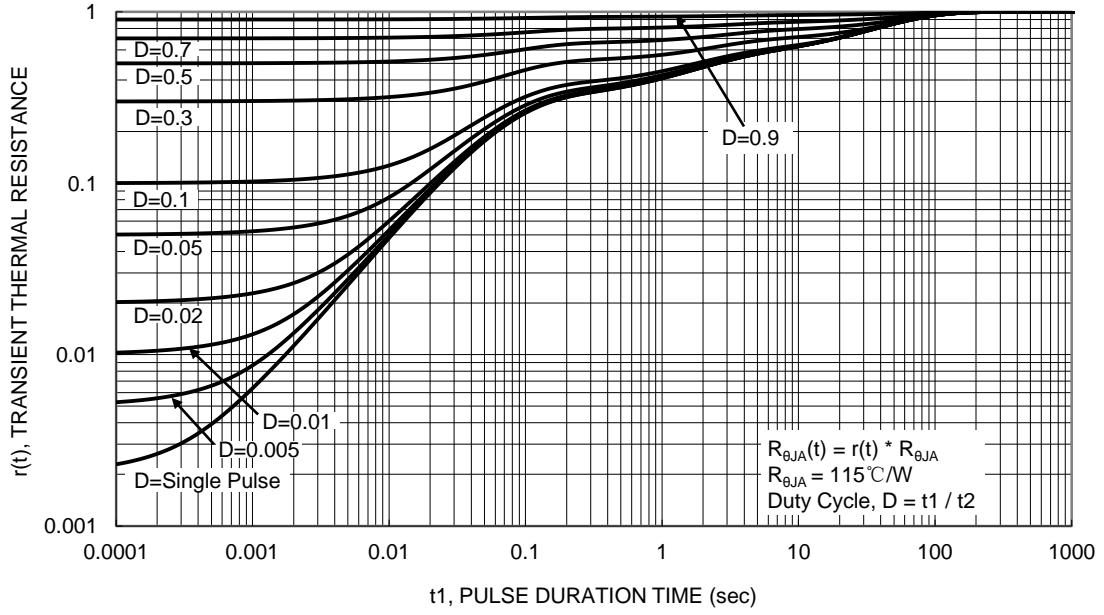
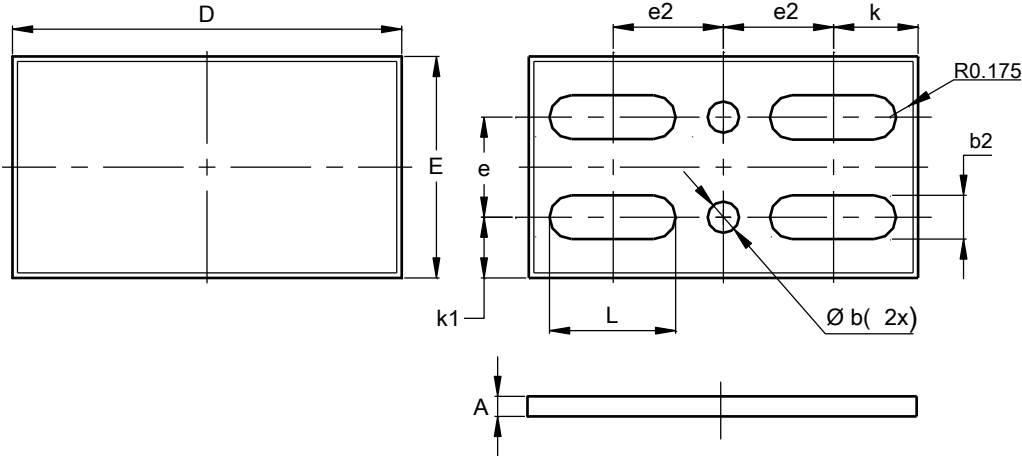


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN3118-6

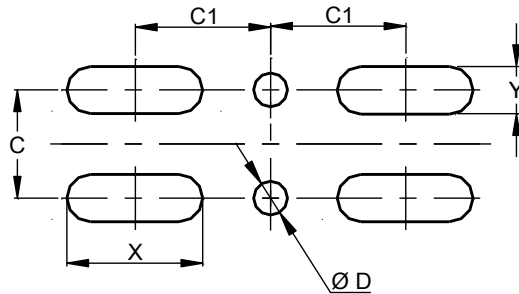


X4-DSN3118-6			
Dim	Min	Max	Typ
A	0.09	0.16	0.11
b	--	--	0.25
b2	0.32	0.38	0.35
D	3.00	3.10	3.05
E	1.72	1.82	1.77
e	--	--	0.800
e2	--	--	0.878
k	--	--	0.648
k1	--	--	0.485
L	0.975	1.035	1.005
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X4-DSN3118-6



Dimensions	Value (in mm)
C	0.800
C1	0.878
D	0.250
X	1.005
Y	0.350

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